



40V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D T _C = +25°C
40V	4.7mΩ @ V _{GS} = 10V	100A

Description and Applications

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

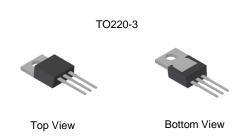
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

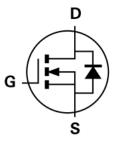
Features

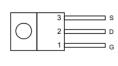
- 100% Unclamped Inductive Switching ensures more reliable and robust end application
- Low Input Capacitance
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: TO220-3
- Case Material: Molded Plastic, "Green" Molding Compound, UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 ⁽³⁾
- Terminal Connections: See Diagram Below
- Weight: 1.85 grams (Approximate)







Equivalent Circuit

Top View Pin Out Configuration

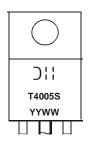
Ordering Information (Note 4)

Part Number	Case	Packaging
DMT4005SCT	TO220-3	50 pieces/tube

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



T4005S = Product Type Marking
T4005S = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 16 = 2016)
WW = Week Code (01 to 53)

DMT4005SCT
Document number: DS38889 Rev. 1 - 2

Downloaded From Oneyac.com



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V_{DSS}	40	V	
Gate-Source Voltage	V_{GSS}	±20	V	
Continuous Dunia Comment (Note C)	T _C = +25°C	I _D	100	А
Continuous Drain Current (Note 6)	$T_C = +70$ °C		85	
Maximum Continuous Body Diode Forward Current (Note 6)	T _C = +25°C	Is	85	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	160	Α	
Avalanche Current, L=0.1mH	I _{AS}	32.5	Α	
Avalanche Energy, L=0.1mH	E _{AS}	52.8	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	P_{D}	2.3	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	52.8	°C/W
Total Power Dissipation (Note 6)	T _C = +25°C	P _D	104	W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	1.2	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

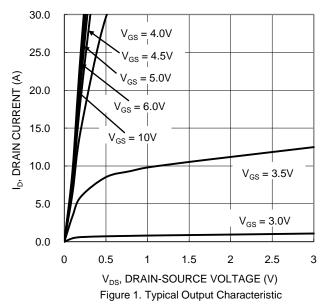
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	40	1	1	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	_	1	1	μΑ	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	1	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(TH)}$	2	_	4	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	3.8	4.7	mΩ	$V_{GS} = 10V, I_D = 50A$	
Diode Forward Voltage	V_{SD}	_	_	1.2	V	$V_{GS} = 0V, I_{S} = 50A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	3062	_		$V_{DS} = 20V$, $V_{GS} = 0V$, $f = 1MHz$	
Output Capacitance	Coss	_	902	1	pF		
Reverse Transfer Capacitance	Crss	_	179	-			
Gate Resistance	R_{G}	_	0.67	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Q_g	_	49.1	_		$V_{DD} = 20V, I_D = 50A,$	
Gate-Source Charge	Q_{gs}	_	10.3	_	nC		
Gate-Drain Charge	Q_{gd}	_	13	_		V _{GS} = 10V	
Turn-On Delay Time	t _{D(ON)}	_	8.7	1		$V_{DD} = 20V, V_{GS} = 10V,$ $I_{D} = 50A, R_{G} = 3\Omega$	
Turn-On Rise Time	t _R	_	6.8		ns		
Turn-Off Delay Time	t _{D(OFF)}	_	18.6	_	115		
Turn-Off Fall Time	t _F	_	7.3	_			
Reverse Recovery Time	t _{RR}	_	31.8	_	ns	I _F = 50A, di/dt = 100A/µs	
Reverse Recovery Charge	Q _{RR}	_	26.5	_	nC	71F = 50A, α/αι = 100A/μS	

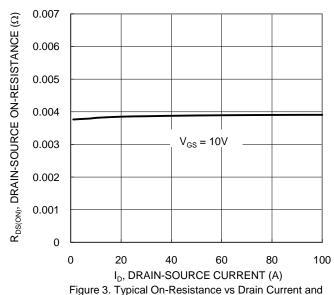
Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

- 6. Device mounted on infinite heat sink.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.

DMT4005SCT
Document number: DS38889 Rev. 1 - 2







Gate Voltage

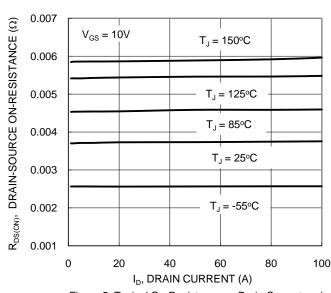


Figure 5. Typical On-Resistance vs Drain Current and Temperature

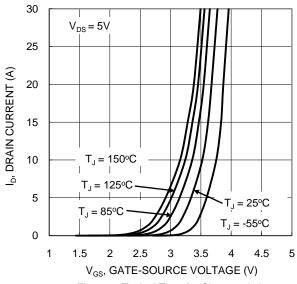
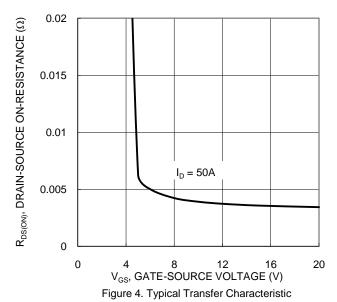


Figure 2. Typical Transfer Characteristic



1.8 $R_{\mathrm{DS(ON)}}$, DRAIN-SOURCE ON-RESISTANCE (NORMALIZED) 1.6 1.4 $V_{GS} = 10V, I_{D} = 50A$ 1.2 1 $V_{GS} = 10V, I_{D} = 20A$ 8.0 0.6 -50 -25 25 50 75 100 125 T., JUNCTION TEMPERATURE (°C)

Figure 6. On-Resistance Variation with Temperature



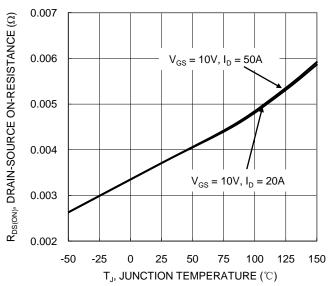
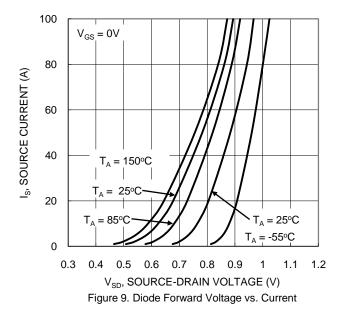
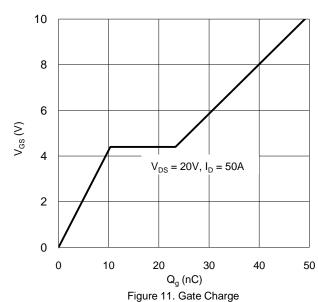


Figure 7. On-Resistance Variation with Temperature





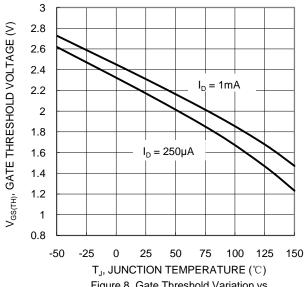


Figure 8. Gate Threshold Variation vs
Temperature

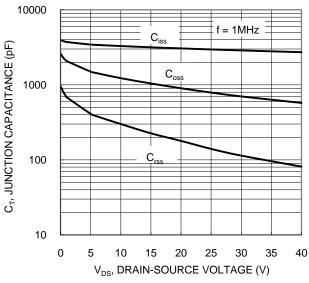
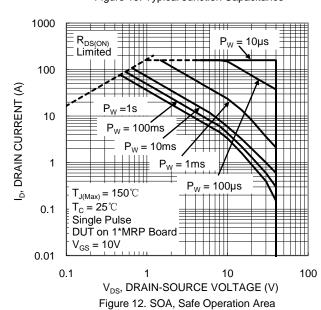


Figure 10. Typical Junction Capacitance





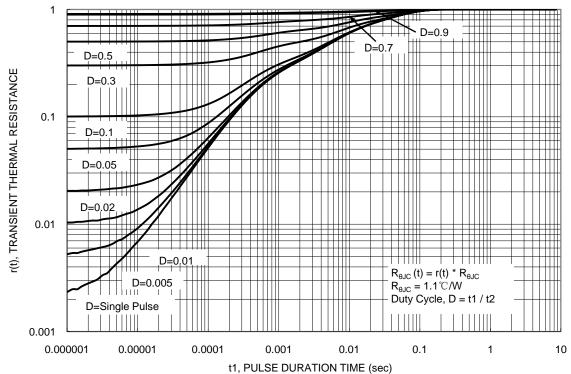
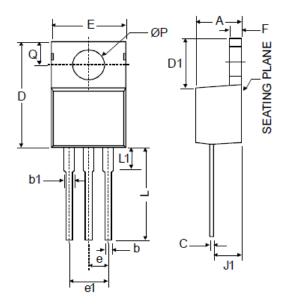


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO220-3



TO220-3				
Dim	Min	Max		
Α	3.55	4.85		
b	0.51	1.14		
b1	1.14	1.78		
С	0.31	1.14		
D	14.20	16.50		
D1	5.84	6.86		
Е	9.70	10.70		
е	2.79	2.99		
e1	4.83	5.33		
F	0.51	1.40		
J1	2.03	2.92		
L	12.72	14.72		
L1	3.66	6.35		
Р	3.53	4.09		
Q	2.54	3.43		
All Dimensions in mm				



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2016, Diodes Incorporated

www.diodes.com

DMT4005SCT

Document number: DS38889 Rev. 1 - 2

Downloaded From Oneyac.com

单击下面可查看定价,库存,交付和生命周期等信息

>>Diodes Incorporated(达迩科技(美台))